

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: ONO, Yoshinobu et al Conf.:
Appl. No.: NEW Group:
Filed: January 17, 2002 Examiner:
For: METHOD FOR FABRICATING III-V COMPOUND
SEMICONDUCTOR

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

January 17, 2002

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amend the claims as follows:

4. (Amended) A method for fabricating a III-V Group compound semiconductor as claimed in claim 1, further comprising a step of forming on the second layer by epitaxial growth at least one $\text{Al}_{y_j}\text{Ga}_{1-y_j}\text{As}$ layer ($0 \leq y_j < 1$, $j=1, 2, \dots$).

REMARKS

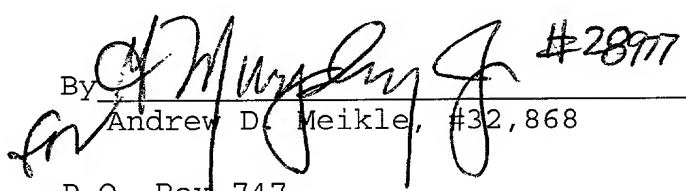
Entry of the above amendments is earnestly solicited. An early and favorable first action on the merits is earnestly solicited.

Attached hereto is a marked-up version of the changes made to the application by this Amendment.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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3885-0103P
Attachments

(Rev. 12/19/01)

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims have been amended as follows:

4. (Amended) A method for fabricating a III-V Group compound semiconductor as claimed in [claim 1, 2 or 3] claim 1, further comprising a step of forming on the second layer by epitaxial growth at least one $\text{Al}_{y_j}\text{Ga}_{1-y_j}\text{As}$ layer ($0 \leq y_j < 1$, $j=1, 2, \dots$).